Unit: mm

TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

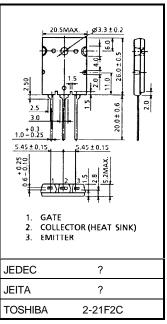
GT80J101B

High Power Switching Applications

- Enhancement mode type
- High speed: t_f = 0.40 μs (max) (I_C = 80 A)
- Low saturation voltage: $V_{CE (sat)} = 2.9 \text{ V (max)} (I_C = 80 \text{ A})$

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-emitter voltage		VCES	600	V	
Gate-emitter voltage		VGES	±20	V	
Continuous collector current	@Tc = 100°C	lc	33	A	
	@Tc = 25°C	ic	80		
Pulsed collector current (Note 1)		ICP	160	Α	
Collector power dissipation	@Tc = 100°C		80	W	
	@Tc = 25°C	PC	200		
	@Ta = 25°C		3.5		
Junction temperature		Tj	150	°C	
Storage temperature		T _{stg}	-55~150	°C	
Screw torque		_	0.8	N⋅m	



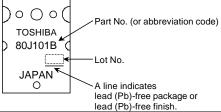
Weight: 9.75 g (typ.)

Note 1: The Maximum rating of I_{CP}=160A is limited by pulse (1ms). Refer to the graph of safe operating area for the detail.

Thermal Characteristics

Characteristics	Symbol	Rating	Unit	
Thermal resistance , junction to case $(\text{Tc} = 25^{\circ}\text{C})$	R _{th (j-c)}	0.625	°C/W	
Thermal resistance , junction to air $(Ta=25^{\circ}C)$	R _{th (j-a)}	35.7	°C/W	

MARKING

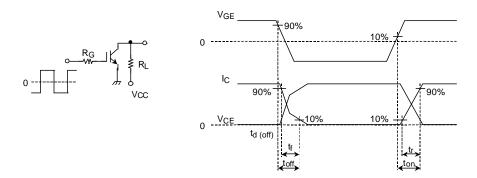


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Electrical Characteristics (Ta = 25°C)

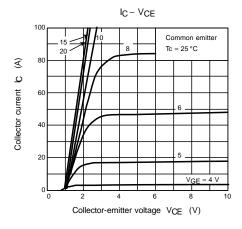
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage current		IGES	V _{GE} = ±25 V, V _{CE} = 0	_	_	±500	nA	
Collector cut-off current		ICES	V _{CE} = 600 V, V _{GE} = 0	_	_	1.0	mΑ	
Gate-emitter cut-off voltage		VGE (OFF)	V _{CE} = 5 V, I _C = 80 mA	3.0	_	6.0	V	
Collector-emitter saturation voltage		VCE (sat) (1)	I _C = 10 A, V _{GE} = 15 V	_	_	2.0	V	
		VCE (sat) (2)	I _C = 80 A, V _{GE} = 15 V	_	2.4	2.9	v	
Input capacitance		C _{ies}	V _{CE} = 10 V, V _{GE} = 0, f = 1 MHz	_	5500	_	pF	
Switching time	Rise time	t _r	Resistive load $V_{CC}=300 \text{ V}, I_C=80 \text{ A}$ $V_{GG}=\pm15 \text{ V}, R_G=33\Omega$ (Note 2)	l	0.3	1	μs	
	Turn-on time	t _{on}		ı	0.5			
	Fall time	tf			0.25	0.40		
	Turn-off time	t _{off}		- 1	0.7			

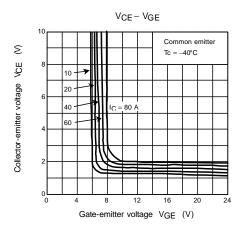
Note 2: Switching time measurement circuit and input/output waveforms.

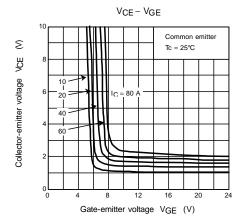


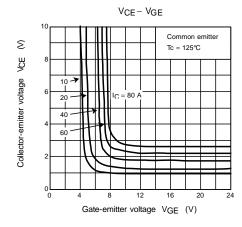
Caution on handling

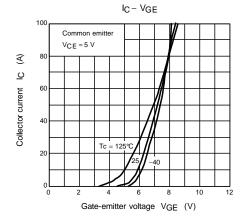
This device is MOS gate type. Therefore, please care about ESD when use.

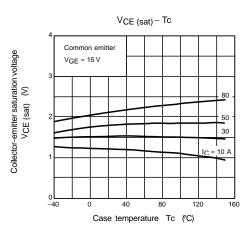


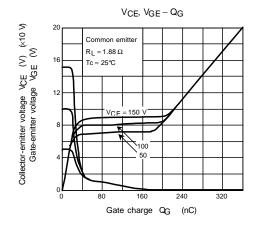


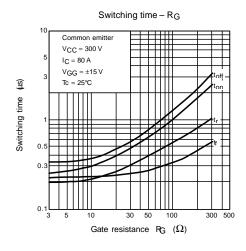


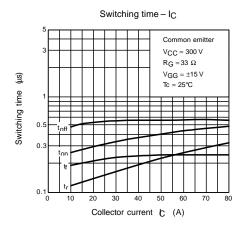


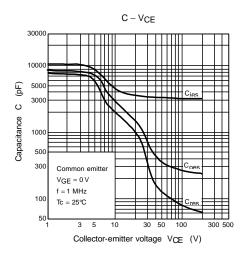


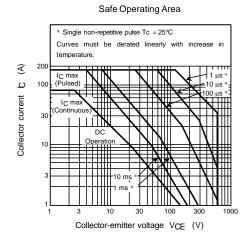


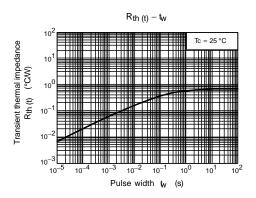


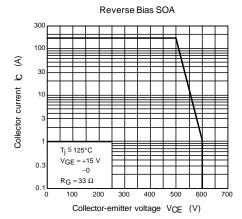












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